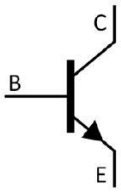
Silicon NPN transistor in a SOT-23 Plastic Package.

Large current capacity and wide ASO.

Small signal general purpose amplifier applications.



PIN1

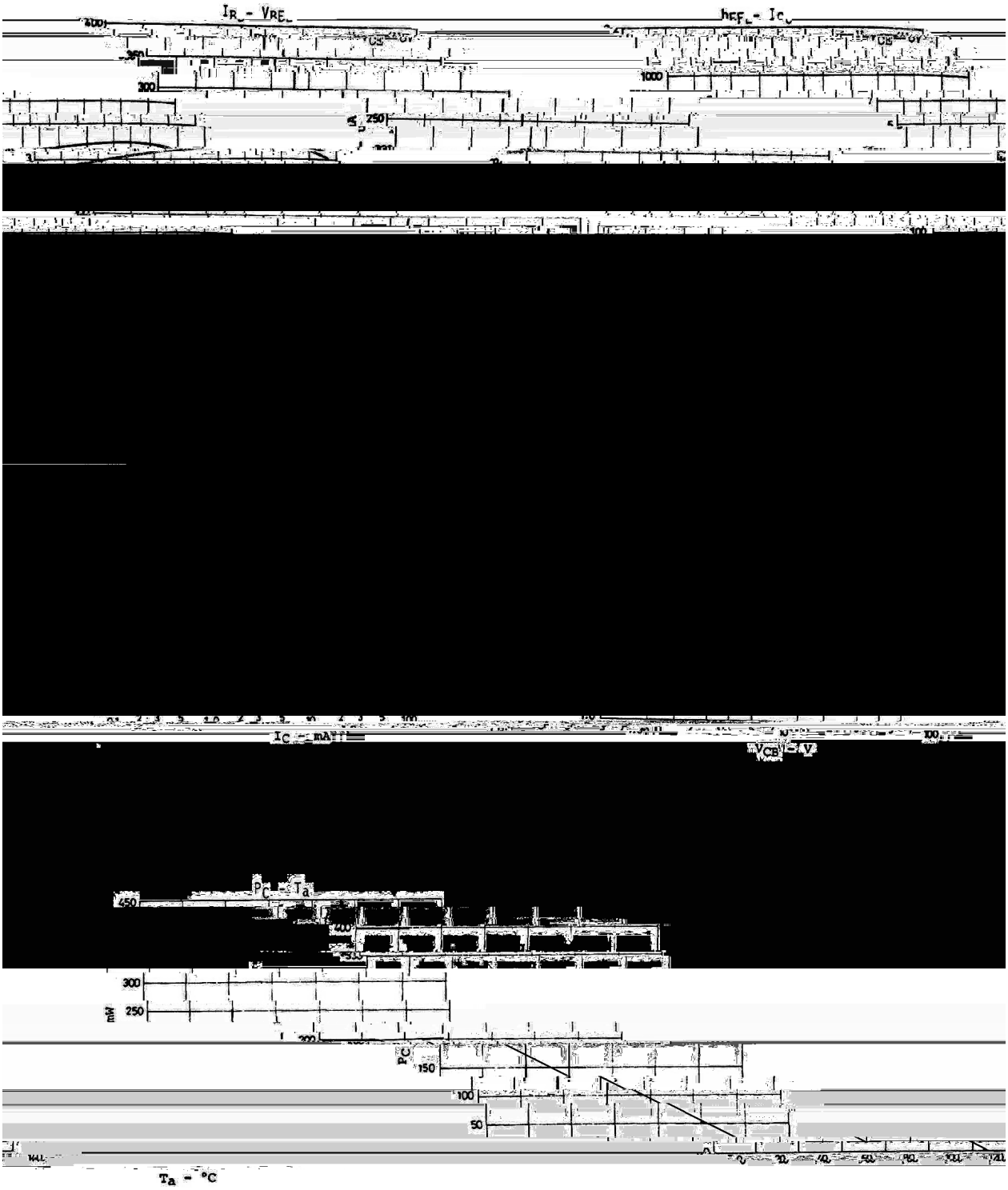
/ Absolute Maximum Ratings(Ta=25)

Parameter		Symbol	Rating	Unit
Collector to Base Voltage	2SC536M 2SC536KM	V_{CBO}	40 55	V
Collector to Emitter Voltage	2SC536M 2SC536KM	V_{CEO}	30 50	V
Emitter to Base Voltage		V_{EBO}	5.0	V
Collector Current		I_C	100	mA
Collector Current(pulse)		I_{CP}	300	mA
Collector Power Dissipation		P_C	250	mW
Junction Temperature		T_j	150	
Storage Temperature Range		T_{stg}	-55 150	

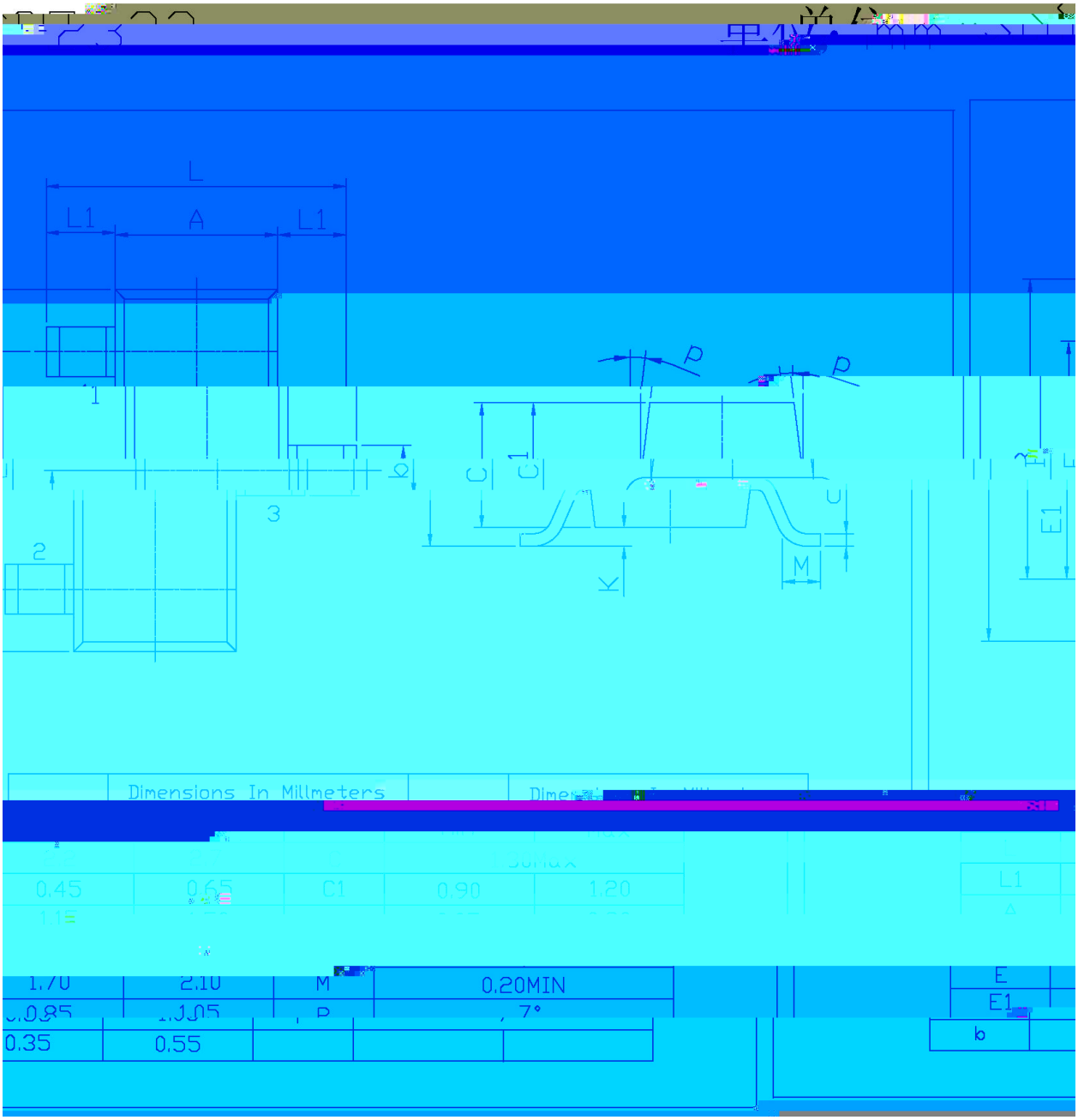
/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-Off Current	I_{CBO}	V_{CB}=35V I_E=0			1.0	μA
Emitter Base Cut-Off Current	I_{EBO}	V_{EB}=4.0V I_C=0			1.0	μA
DC Current Gain	h_{FE}	V_{CE}=6.0V I_C=1.0mA	60		960	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=50mA I_B=5.0mA			0.5	V
Transition Frequency	f_T	V_{CE}=6.0V I_C=1.0mA		100		MHz
Collector Output Capacitance	C_{ob}	V_{CB}=6.0V I_E=0 f=1.0MHz		3.5		pF
Collector- Base Time Constant	C_C.rbb′	V_{CB}=6.0V I_c=1.0mA f=31.9MHz		250		pS

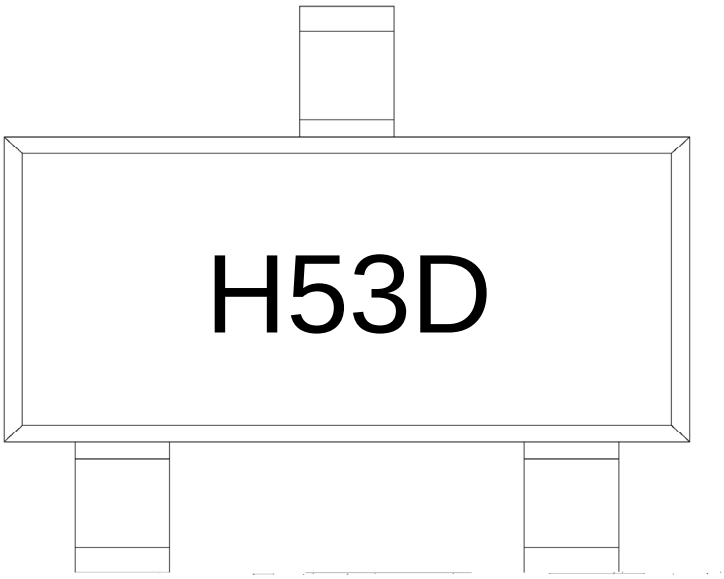
/ Electrical Characteristic Curve



/ Package Dimensions



/ Marking Instructions



h_{FE}

Note:

Company Code

Product Type Code

h_{FE} Classifications Symbol Code

2SC536M/KM

Rev.F Apr.-2017

DATA SHEET